

ABSTRACT OF THE DISCLOSURE

To provide a dry etching method that attains a high selectivity to a mask and a high etch rate simultaneously, in the steps of forming an intermediate  
5 layer and a patterned resist layer on an organic film and etching the organic film using a plasma of a gas containing either of nitrogen and hydrogen, a metal or a metal nitride is used as a part of the intermediate layer.

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TOPIC: 8262860